

Gold Stud Bump Flip Chip Bonding on Molded Interconnect Devices

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Abstract

A molded interconnect device (MID) is an injection molded thermoplastic substrate which incorporates a conductive circuit pattern and integrates both mechanical and electrical functions. The thermoplastic material is doped with a metal-plastic additive which can be activated by laser. A laser beam is pointed on the surface of the injection molded plastic to form a metallization track by aggregating the metal additives. The metallized path is then plated with copper, nickel and gold finishes subsequently. MID Technology offers great advantages in design flexibility, device miniaturization, and true 3D integration of complex shapes.

Flip chip bonding of bare die on MID can be employed to fully utilize MID's advantage in device miniaturization. Compared to the traditional soldering process, thermo-compression bonding with gold stud bumps provides a clear advantage in its fine pitch capability. However, challenges also exist. Few studies have been made on thermocompression bonding on MID substrate, accordingly little information is available on process optimization, material compatibility and bonding reliability. Unlike solder reflow, there is no solder involved and no "self-alignment," therefore the thermo-compression bonding process is significantly more dependent on the capability of the machine for chip assembly alignment.

This paper presents the studies on flip chip thermo-compression bonding (TCB) of gold stud bumps on MID substrate. Non-conductive paste (NCP) is applied on the MID substrate before attachment of bare dies, and subsequently the dies are compressed at elevated temperatures to bond the gold stud bumps to the substrate pads and to cure NCP simultaneously. Daisy chained test vehicles were designed and built to demonstrate this process with multiple assembly challenges resolved. The test vehicles successfully passed long term reliability testing based on IPC standard IPC-SM-784, although the substrate bond pads experienced excessive deformation during the thermo-compression bonding process at higher bonding forces. Regardless of the bonding forces evaluated, a certain degree of atomic bonding is observed between gold stud and gold plating on the substrate, However, such small scale bonding is not adequate to secure the chip in place, the assembly relies on the contraction of non-conductive paste during the cure process to maintain a reliable bonding interface. Based on reliability test results, the bonding force can be further reduced to minimize the substrate pad deformation while maintaining bonding reliability.

Key words: Molded interconnect device, MID, Flip chip, Thermocompression bonding, TCB, Reliability, Laser direct structuring, LDS.

Introduction

A molded interconnect device (MID) is an injection molded thermoplastic substrate which incorporates a conductive circuit pattern and integrates both mechanical and electrical functions (1). The thermoplastic substrate is doped with a metal-plastic additive which can be activated by laser to form the metallized path. The metallized path is then plated with copper, nickel and gold finishes successively. There are mainly three variations of MID fabrication process: one shot injection molding, two shot injection molding, and insert molding. MID technology offers great advantages in design flexibility, device miniaturization, and true 3D integration of complex shapes.

Flip chip bonding of bare die on MID can be employed to fully utilize MID's advantage in device miniaturization. Compared to the traditional soldering process, thermo-compression bonding (TCB) with gold stud bumps provides a clear advantage in its fine pitch capability. However, challenges also exist.

Few studies are made on thermocompression bonding on MID substrate, accordingly little information is available on process optimization, material compatibility and bonding reliability. Unlike solder reflow, there is no solder involved and therefore no “self-alignment.” Accordingly the thermo-compression bonding process is significantly more dependent on capability of the machine for chip assembly alignment.

This paper presents the studies on flip chip thermo-compression bonding of gold stud bumps on the MID substrate. The purpose of the study is to demonstrate the stud bump bonding process on the MID substrate and at the same time to understand the fundamentals of the bonding process to assist process optimization.

Experimental

There are a variety of methods to make molded interconnect devices. For this experiment, one short injection molding method is used. The process is described in Figure 1 (2). The MID material supplier provided the MID substrate made from glass fiber filled PPA compounds with metallized traces for this evaluation.

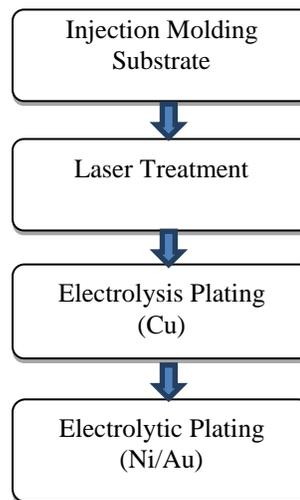


Figure 1: MID fabrication process (2)

Figure 2 shows the evaluation process for the flip chip Thermocompression bonding on MID substrate. Test boards and dies are designed with daisy chains to check electrical continuity after flip chip thermocompression bonding. A production stud bumping machine was used to bump gold studs on the silicon wafers which were then sawed into individual dies. Shear testing was performed to examine the integrity of the gold stud bumps. The thermocompression bonding process was done using a production flip chip bonder. Non-conductive paste (NCP) was at first dispensed on the MID substrates, the dies were compressed against the substrates while the temperature was quickly ramped to preset value and held for a very short duration. After bonding, the assemblies were checked in terms of daisy chain continuity, bump to pad alignment and voids in the NCP material. Reliability testing was done on the assemblies based on IPC standard SM-784, including high temperature aging, high temperature/high humidity and temperature cycling (3). Cross sectioning was used to examine the bump height and bonding interface integrity.

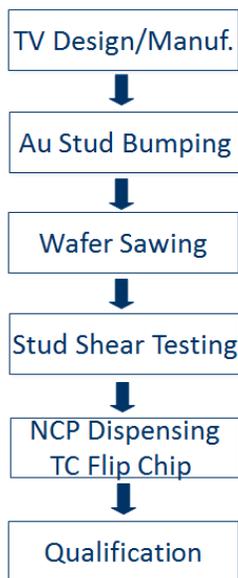
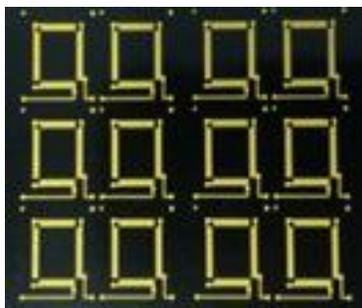


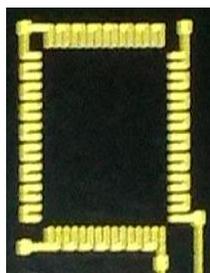
Figure 2: Thermocompression bonding evaluation process.

Figure 3 shows the test vehicle design. The MID substrate is made from a commercial laser direct structuring (LDS) material with a thickness of 2.0mm. After laser beam structuring and copper electrolysis plating, a minimal 120 micro inch electrolytic nickel was deposited on the substrate followed by a minimum 1.0 micro inch flash gold. The line width is 0.15mm and the spacing between lines is 0.20mm. The pitch between bond pads is 0.35mm.

For the dies, the die size is 6.5mm x 6.0mm with thickness 0.42mm. The bond pad opening for the gold stud bump is 75 x 150um. There are a total 64 bumps on each die.



Test board design



Test board daisy chained pads



Test die daisy chained pads

Figure 3: Daisy chained test vehicle design

Figures 4 to 6 show the processes of gold stud bumping, NCP dispensing and flip chip bonding. All the work was done at the facility of the bonding machine supplier. The gold stud bumping process is similar to the gold ball bonding process, with the only difference being that after the bonding process the gold wire is cut off at the neck by squeezing the tail between the capillary edge and bump to create a stud.

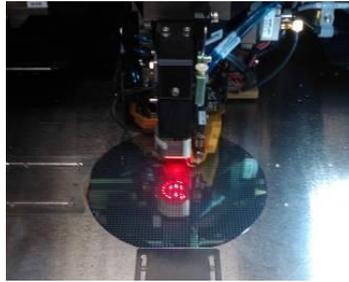


Figure 4: Gold stud bumping process

Before the thermocompression bonding process, the NCP material was dispensed on the substrate. During the flip chip bonding process, a collet picked up the die and then the machine automatically aligned the die to the substrate. A pre-set force was then applied on the die to squeeze out the NCP material to ensure an intimate contact between gold bumps and substrate pads, while the temperature ramped up quickly to a preset value and the temperature maintained for a short period of time to form bonds between gold studs and pads while simultaneously curing the NCP material.

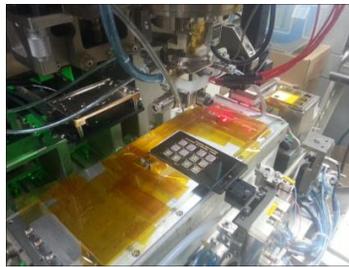


Figure 5: NCP dispensing process.



Figure 6: Flip chip bonding process.

In order to examine the effect of the bonding force on the bonding interface integrity, five bonding forces from 1kg to 5kg are evaluated in the experiment, accordingly forces per pad are: 15.6g, 31.2g, 46.9g, 62.5g, and 78.1g respectively.

Non-conductive paste (NCP) is applied during the flip chip bonding process. It needs to be cured while the bonding is formed. Differential scanning calorimetry (DSC) was used to characterize the cure properties of NCP at temperature ramp. The percentage of cure is determined by comparing the heat of cure of partially cured resin with fully cured resin. Table 1 shows the measurement results on the NCP material. At 235°C for 12 seconds, a cure percentage of 93% can be achieved.

Table 1: DSC measurement of NCP material.

Curing condition		DSC results	
Temperature (°C)	Time (s)	$\Delta H(J/g)$	Cured Percentage (%)
25	0	-135.40	0
235	8	-15.33	88.68
235	10	-10.91	91.94
235	12	-8.74	93.54

Based on DSC measurements, the flip chip bonding parameters were finalized. Figure 7 shows the actual temperature measurement process. A thermocouple was attached to the center of footprint of pads for the measurement. Figure 8 shows the actual temperature profile for the bonding process. A temperature profile of 235-240 °C for >12 seconds can be achieved to satisfy the NCP curing requirement.

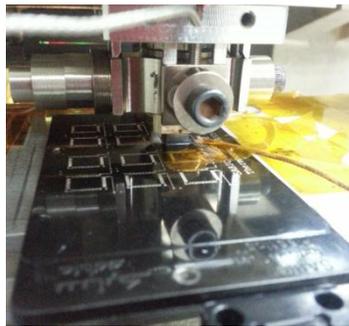


Figure 7: TCB bonding temperature measurement.

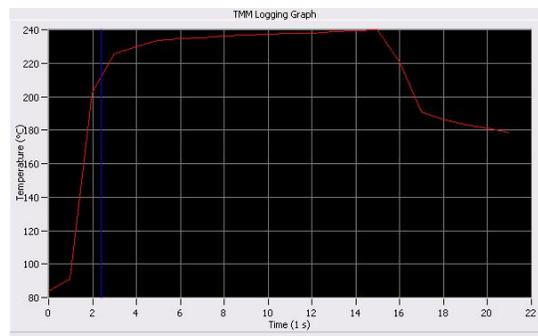


Figure 8: Actual temperature profile for the bonding process.

Results and Discussions

Gold wires with a diameter of 1 mil are used for the experiment. After bumping, the diameter, height and shear forces of the bumps were measured. Figure 9 shows a typical gold stud bump.

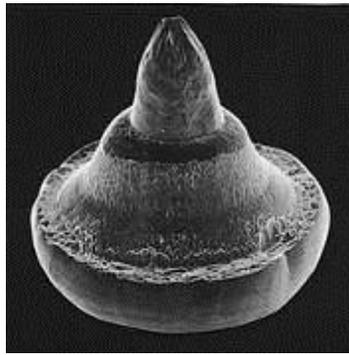


Figure 9: Gold stud bump.

Table 2 gives the measurements results on the gold stud bumps. The preset requirements are derived either by the physical constrains or standard requirements (4). Tight process control is achieved as reflected from Cpk values.

Table 2: Gold stud bump characteristics

	Bump diameter (um)	Bump height (um)	Shear force (g)
Min.	66.9	40.0	29.86
Max	69.4	42.9	35.45
Mean	67.85	41.42	32.14
Requirement	63.5-75	Min. 30	Min. 20.6
Cpk	2.73	6.39	3.99

After flip chip thermocompression bonding, the continuity of daisy chains was checked without showing any opens. X-ray imaging showed all the bumps were bonded to the center of pads without obvious misalignment. C-SAM demonstrated that there was no void at the bonding areas. Figure 10 shows post bonding inspection results.

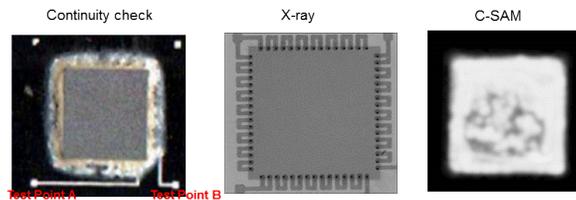


Figure 10: Post bonding inspection (continuity check, X-ray imaging and C-SAM)

Figure 11 shows the optical photos of cross sectioned samples bonded at the bonding force of 87.1grams per pad. It is expected that the soft gold stud bump will deform under the compressive forces; however, significant deformation of substrate pads is observed. More seriously some pads show breakage and cracks. This raises serious concern on the bonding interface integrity and long term reliability.

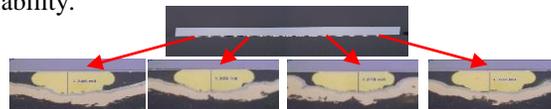


Figure 11: Substrate pad deformation during the TCB process.

In order to compare how the bonding forces affect the pad deformation, cross sectioning on assemblies with other bonding forces was performed. Figure 12 shows typical bonding interfaces at different bonding forces under SEM. Pad deformation can be clearly observed for the bonding force of 31.2 grams per pad and above. Significant pad breakage and crack can also be clearly observed. At the lower force, 15.6 grams per pad, no obvious pad deformation is observed.

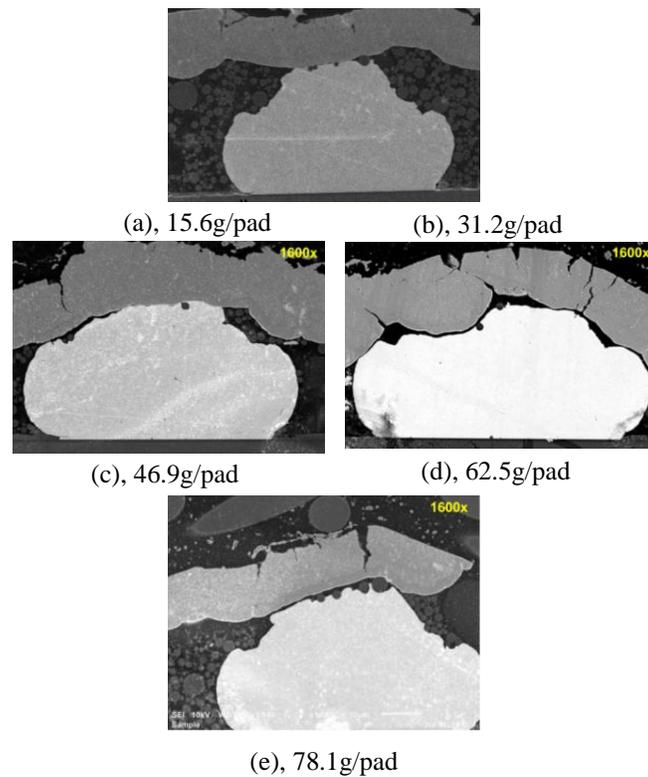


Figure 12: Deformation of substrate pads during thermocompression bonding

Multiple factors could be responsible for the deformation of pads: bonding force, bonding temperature, MID substrate material, and plating quality. As shown in the previous photos, a high bonding force causes more deformation of pads. A high bonding temperature is necessary to form bonds between gold studs and pads and to fully cure the NCP resin (5); however, it is found that the bonding temperature (240°C) is close to the softening temperature of the NCP resin with a HDT temperature at 263°C (6). Under the flip chip bonding conditions, the NCP substrate may not provide adequate mechanical support to the pads, especially when the stress is mainly concentrated on the tips of the gold studs. Accordingly the pads deform under compressive load with the contact areas deforming the most. The metal trace on the MID substrate is made through the electrolytic plating process after laser structuring of the substrate resin. The roughness of the substrate surface after laser structuring will affect the plating uniformity, which then affects the bonding interface integrity and makes the traces more prone to crack and breakage.

From the cross sectioning, no obvious deformation is observed on the bulk of the gold studs, except the tips of the studs, due to softening of the MID substrate at the bonding temperature. The small contact area between gold studs and deformed substrate pads raises a concern about bonding reliability in terms of whether metallic bonding is formed at the contact interface. Figure 13 shows the contact interface between gold studs and substrate pads under very high magnification for all the bonding forces evaluated. All the samples show some degree of metallic atomic bonding, a continuous path between the flash gold plating and the gold stud, regardless of the width of the area successfully joined, although gaps between gold studs and substrate pads exist for more areas.

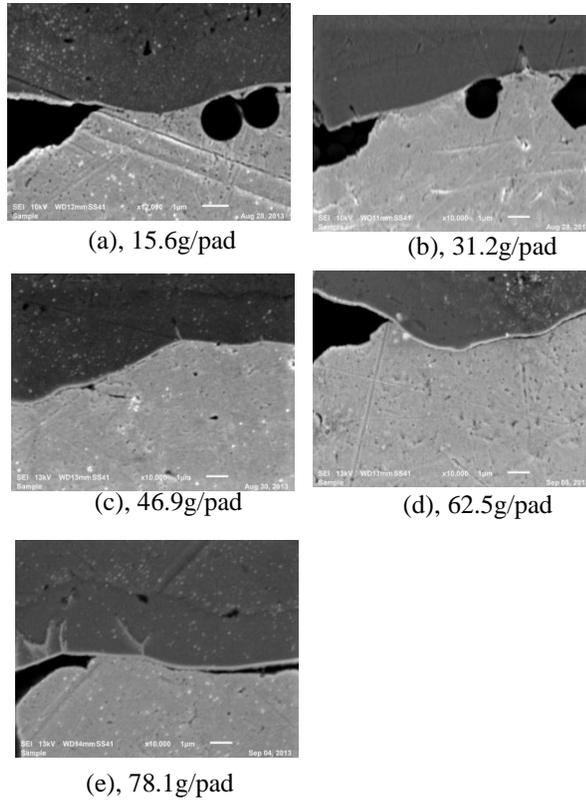
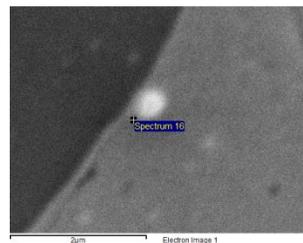
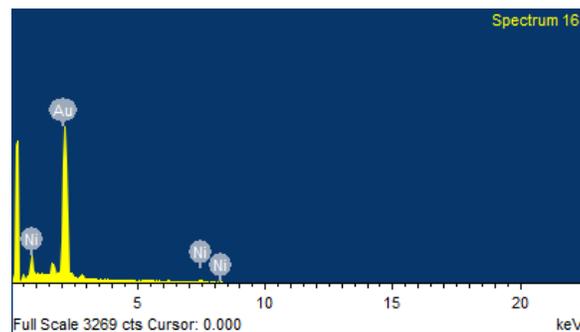


Figure 13: Bonding between Au stud and substrate pad Au plating at different bonding forces

The gold-gold atomic bonding is accompanied by the formation of a thin intermetallic layer, as shown in the EDX measurement (Figure 14). EDX analysis suggests a formula of Au_3Ni . The intermetallic layer is not clear in the SEM images; deductions made from the EDX spectra within this report suggest it is rarely more than 0.1nm thick and never more than 0.3nm thick.



(a), EDX measurement spot



(b), EDX measurement spectrum

Figure 14: EDX measurement on the bonding interface.

Although there is a certain degree of bonding between the gold stud and gold plating, the tiny bonding area may not be strong enough to secure the chips in place. To examine this, we purposely bonded a few samples without dispensing the NCP material. After the process, the chips fall off easily without using external forces. Therefore NCP material is essential for the thermocompression bonding process. The contraction of NCP material during curing causes a compressive stress on the contact interface to enable a reliable bonding interface between gold stud bumps and substrate pads.

After the thermocompression bonding process, reliability tests were done based on IPC-SM-784 standard (3):

- Thermal cycling: -55°C ~ +125°C (1000cycles).
- Humidity test: 85°C/85%RH (500hours).
- High temperature storage: 125 °C (500 hours).

Due to limited samples available, the reliability was only performed on samples with selected bonding forces.

- 78.1g/pad: 10 samples each for all above three tests.
- 46.9g/pad: 3 samples for temperature cycling.
- 15.6g/pad: 3 samples for temperature cycling.

After prolonged testing, the continuity of all the samples was checked. No opens were detected. This demonstrated that the samples bonded with lower forces can have the same reliable bonding interface as the samples with higher forces. It is possible to optimize the bonding force to reduce the substrate pad deformation while maintaining bonding reliability.

Summary

The flip chip thermocompression bonding has been successfully demonstrated on the molded interconnect device substrate.

Significant pad deformation and cracks during the thermocompression flip chip bonding process were observed, primarily due to high bonding temperature and bonding force, and softening of MID substrate material at the elevated bonding temperature.

A certain degree of gold to gold bonding is formed at the bonding tips and surrounding areas for all the evaluated forces. However, the tiny bonding area does not provide adequate strength to secure chips in place; contraction of NCP during curing is essential for a stable interconnect.

Bonding force needs to be further optimized to reduce the substrate pad deformation while maintaining a stable and reliable bonding interface.

Acknowledgments

The authors would like to thank the following companies: Sabc for providing metallized MID substrates, Nagase for providing NCP material and ASM Hong Kong for providing equipment for the evaluation work.

References

- 1) Molded Interconnect Device International Association (<http://www.3d-mid.de/>).
- 2) 3-Dimensional Circuitry Laser Direct Structuring Technology for Moulded Interconnect Devices, LPKF. (http://www.lpkf.com/_mediafiles/1797-lpkf-lds-process.pdf).
- 3) IPC Standard SM-784, "Guidelines for Chip-on-Board Technology Implementation," 1990.
- 4) JESD22-B116A, "Wire Bond Shear Test," 2009.
- 5) Wei, J., F. Ang, G.G. Zhang, Z. Chen and C.C. Wong, "Temperature and Pressure Dependence in Thermocompression Gold Stud Bonding," SMITech Technical Reports, Volume 8, Number 1, Jan-Mar 2007.
- 6) Sabc, LDS Substrate Material Properties, 2013.

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OUTLINE

- **Introduction to MID Technology**
- **Flip chip Gold Stud Thermocompression Bonding**
- **Evaluation Process Flow**
- **Process Evaluation and Optimization**
- **Reliability Evaluation**
- **Summary**

INTRODUCTION

A molded interconnect device is an injection molded plastic substrate which incorporates a conductive circuit pattern and integrates both mechanical and electrical functions

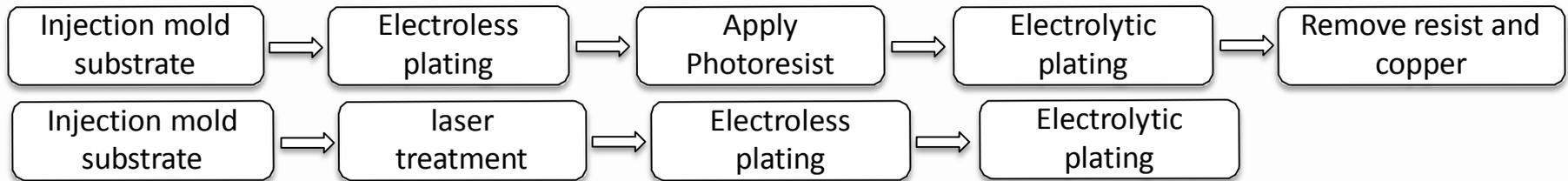
-- Molded Interconnect Device International Association



* Photo courtesy of LPKFUSA.com and 3D-MID.de

MID Manufacturing Process

•One Short Injection Molding



•Two Short Injection Molding

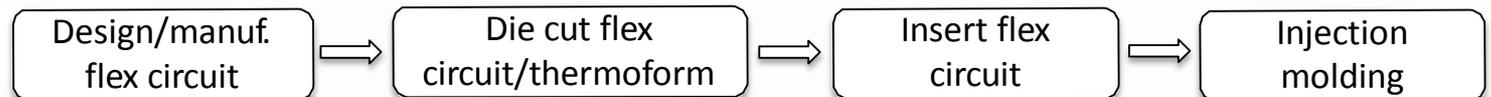


•Insert Molding

Hot stamping



Capture process



MID Benefits

- 3D manufacturing of complex shapes
- Simplified manufacturing process
- Component integration through 3D circuitry
- Miniaturization of products

MID Challenges

- Low circuit density: top layer and bottom layer, large line spacing
- Limited LDS material selection
- Proprietary laser direct structuring technology (LPKF)
- Limited plating resources
- Component assembly
 - Soldering components
 - Flip chip bonding
 - Wire bonding

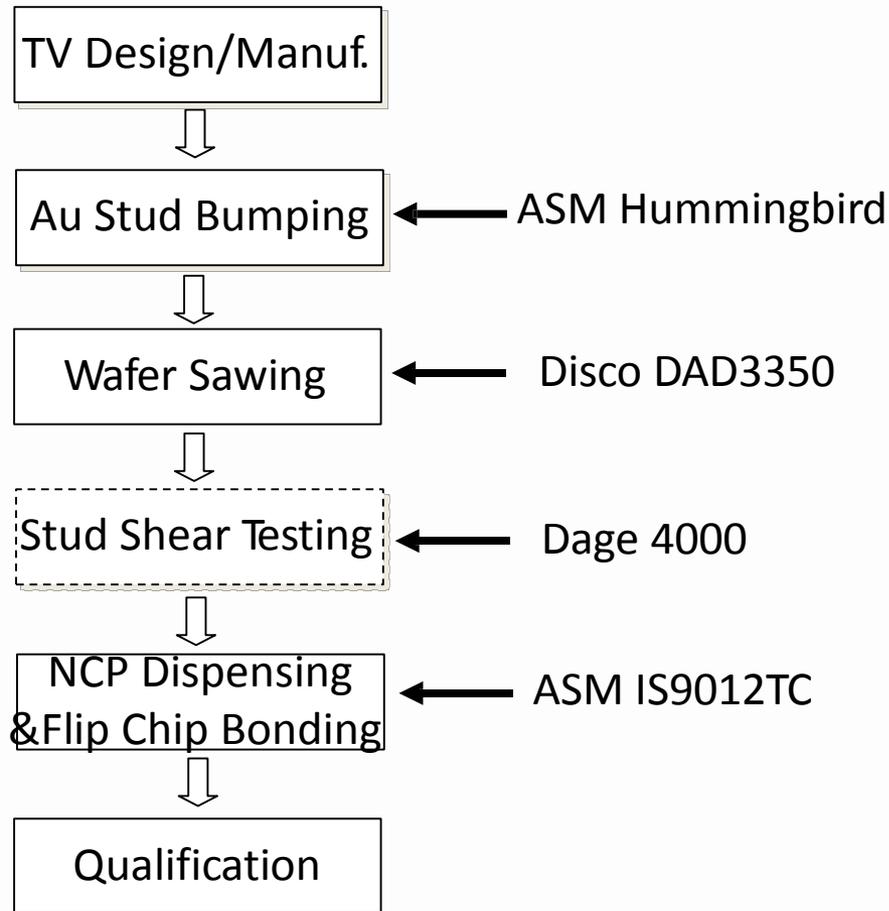
MID Assembly Challenges

- Soldering
 - Solder paste stencil printing on curved surface topology
 - Attach components on non-flat surfaces
 - Attach components on vertical surfaces
 - MID substrate thermoplastic compatibility with lead free process
- **Flip chip thermo-compression bonding**
 - MID substrate thermoplastic surface flatness and warpage
 - Pad plating roughness
 - MID substrate thermoplastic compatibility with thermocompression bonding temperature and pressure
 - Alignment of chip pad to substrate pad

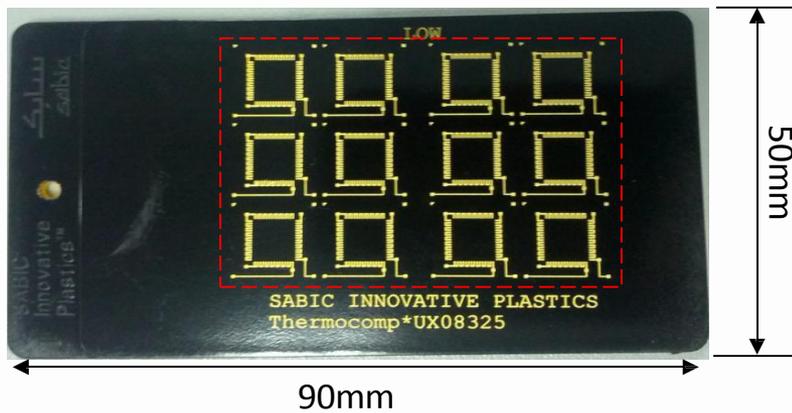
Thermo-compression Bonding

- Thermocompression bonding describes a wafer or silicon bonding technique in which two metals, e.g. gold-gold, are brought into atomic contact to make electrical connections by applying force and heat simultaneously
- Why select thermo-compression bonding
 - Fine pitch capability and device miniaturization
 - Improve electrical performance for RF devices
 - Prevent damage and contamination to sensitive devices

Evaluation Process Flow

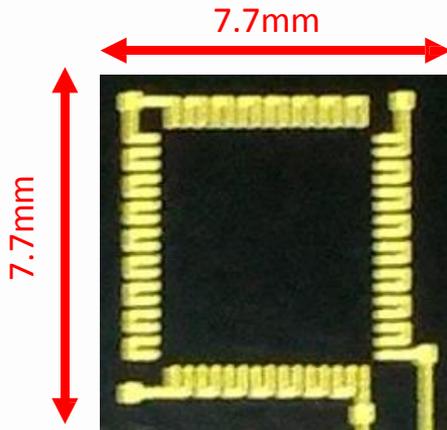


TCB Test Vehicle Design



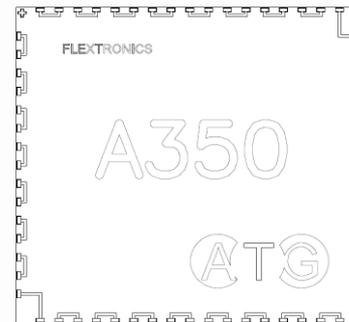
Substrate materials:

- UX08325 Plastic
- Electrolytic Nickel: 3.0um Min.
- Electrolytic Gold: 0.03um Min.



Substrate design:

- Bond Pad size: 150 x 575um
- Bond Pad Pitch: 350um
- Thickness: 2.0mm

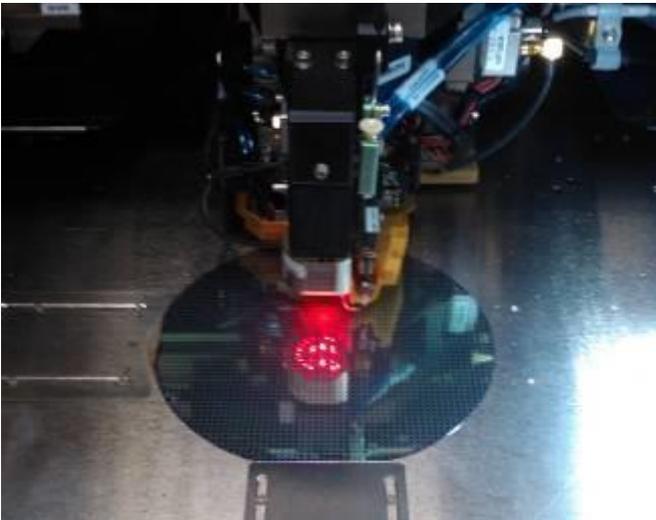


Silicon

- Die Size: 6.5 x 6.0mm
- Die Thickness: 0.42mm
- Bond Pad Pitch: 350um
- Bond pad opening: 75 x 150um
- Total I/O: 64

Gold Stud Bumping

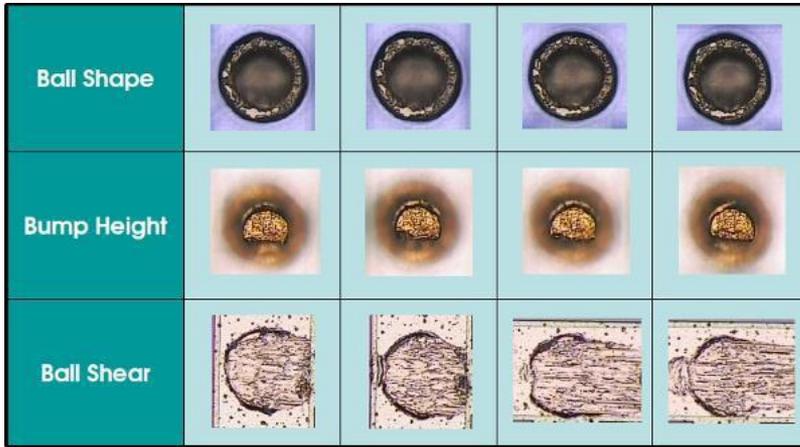
Bumping Process



Gold Stud Bump



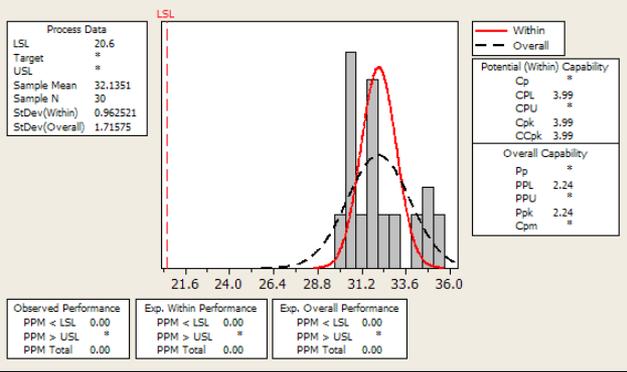
Gold Stud Bump Inspection



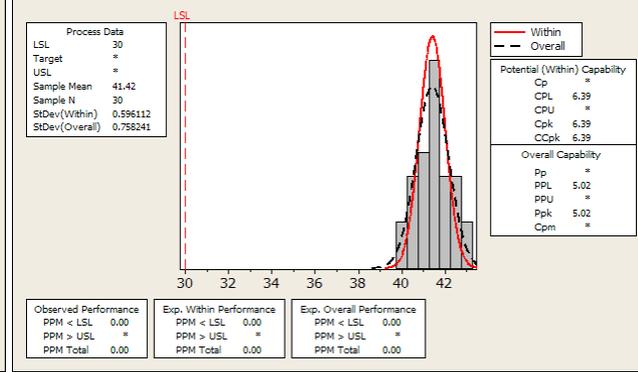
	Bump diameter	Bump height	Shear force
Min. (um)	66.9	40	29.86
Max (um)	69.4	42.9	35.45
Mean (um)	67.85	41.42	32.14
Requirement (um)*	63.5-75	Min. 30	Min. 20.6
Cpk	2.73	6.39	3.99

* Based on physical constrains or JESD22 requirement

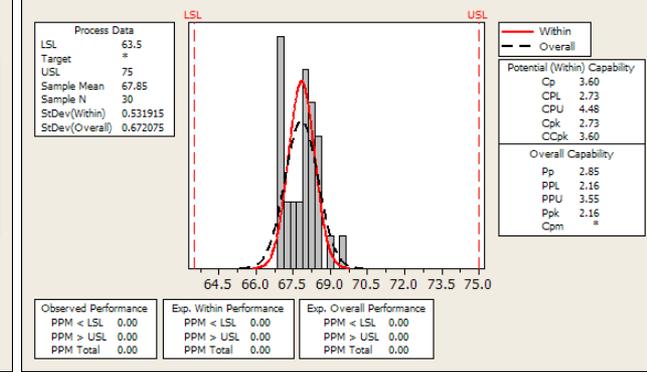
Process Capability of Bump Shear



Process Capability of Bump Height



Process Capability of Bump Size

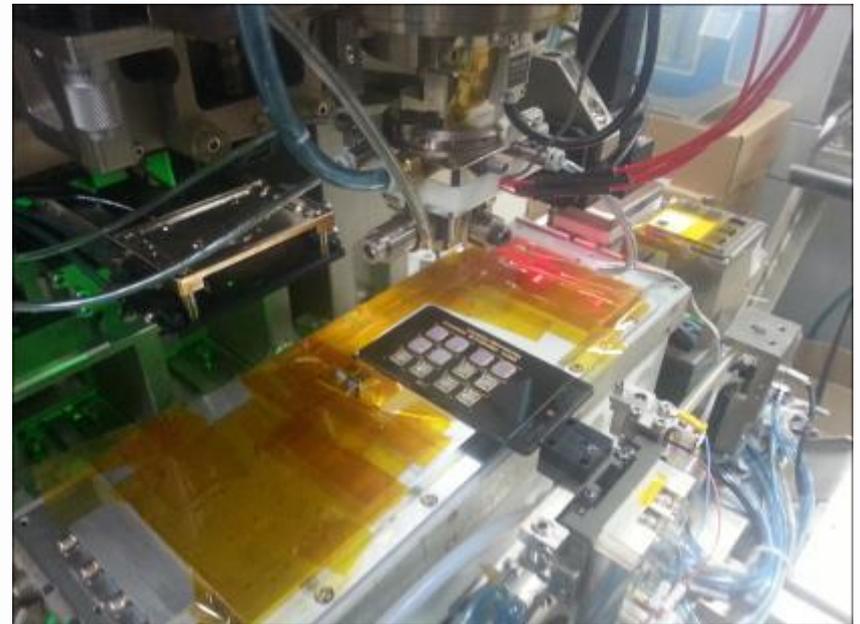


TC Flip Chip Bonding

NCP Dispensing on PCB



TC Flip Chip Bonding



Heat and force are applied simultaneously to bond the metals and at the same time to cure the NCP material

Bonding Parameters

- Bonding parameters for TCB (Bonding temperature, pressure, duration)
 - First experiment: 78.1g per pad (5Kg total for 64 I/Os)
 - Following experiments (force per pad): 15.6g, 31.2g, 46.9g, 62.5g
- Curing profile for NCP (Cure temperature, duration)

NCP Cure Temperature

NCP : Nagase[®] UFR109VP

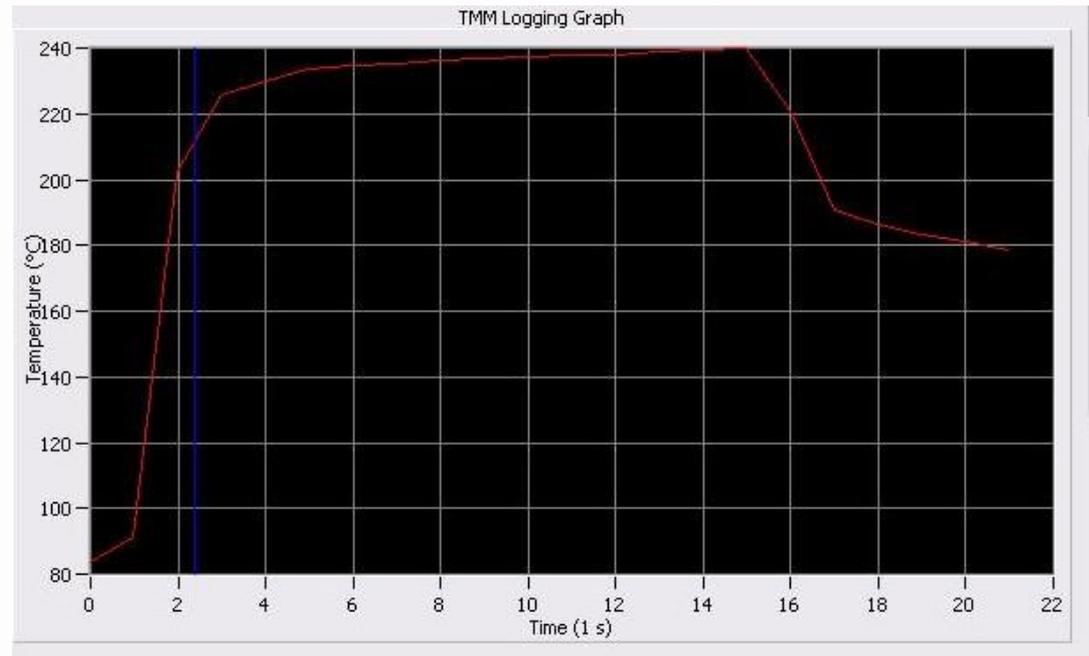
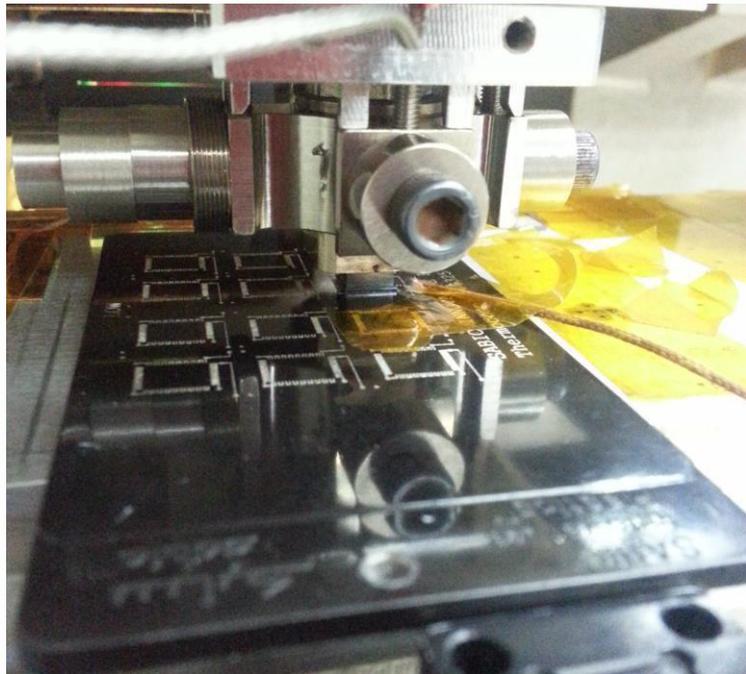
Curing Condition		DSC results	
Temperature (°C)	Time (s)	ΔH (J/g)	Cured Percentage (%)
25	0	-135.40	0
235	8	-15.33	88.68
235	10	-10.91	91.94
235	12	-8.74	93.54



Bonding Parameters

Dispensing Parameters (Musashi Dispensing System)		AD900TC Parameters	
NCP Used	Nagase® UFR109VP	Bond Force	5000 g
Pressure	100kPa	Blow Time	100ms
Vacuum	-1.5kPa	Pick Time	50ms
Nozzle Type	Gage 30	Head Pick Delay	30ms
Dispensing speed	5 mm/s	Arm Bond Delay	50%
Nozzle Length (inch)	1/4	Uplook PR Delay	60ms
Injection Height	150µm	Downlook PR Delay	60ms
Pre-Injection Time	50ms	Bond time	12s
Injection Time	50ms	Bondhead Surface Temperature	315°C
Pre-Stop Time	0ms	Anvil Block Surface Temperature	80°C
Vac delay	15ms		

Actual Temperature Measurement



Temperature profile at the center of bonding footprint

NCP Dispense Pattern



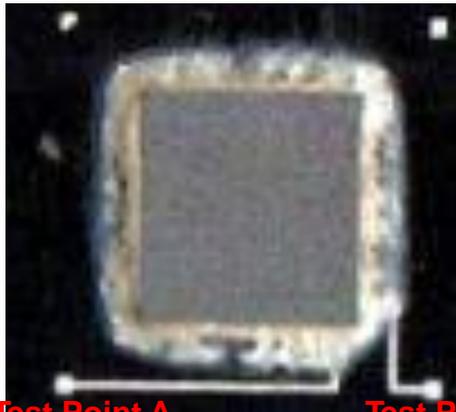
Assembly after TCB



Daisy chain continuity checking

Post Inspection

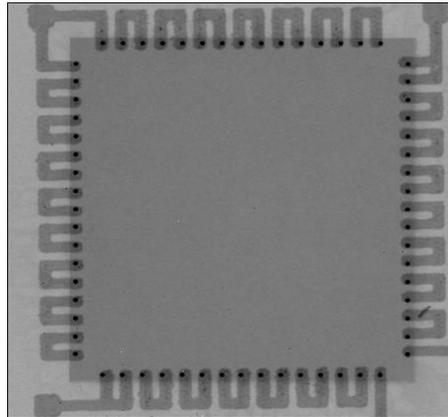
Continuity check



Test Point A

Test Point B

X-ray

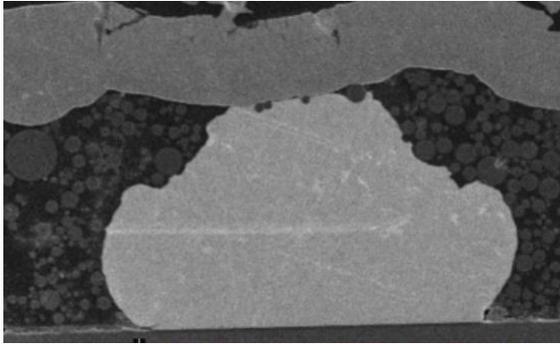


C-SAM

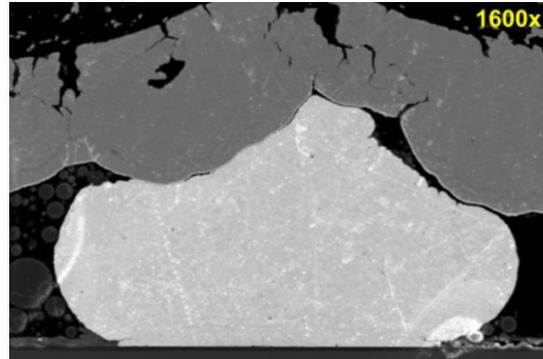


- All bonded units will conduct the O/S test thru point A & B.
- All of bumps were bonded on the bond pad center.
- No-void was observed between die and board on bonding areas.

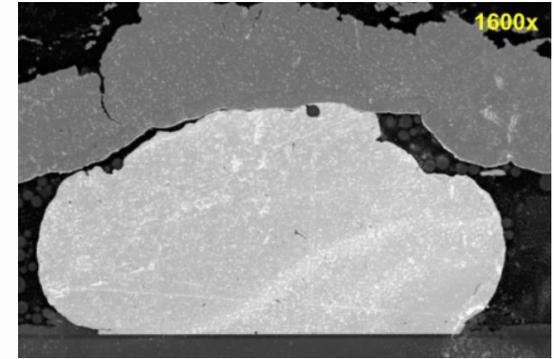
Cross-section Inspection



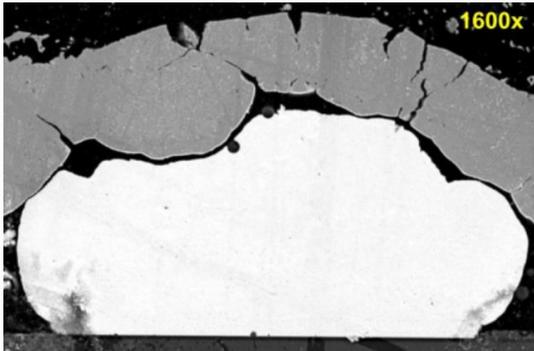
15.6g/pad



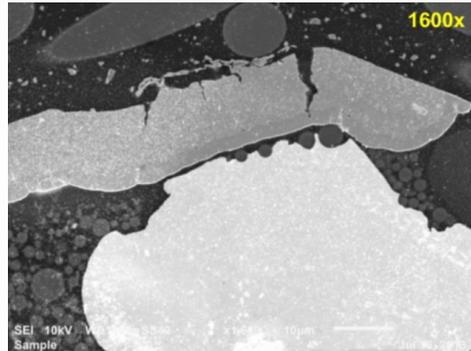
31.2g/pad



46.9g/pad



62.5g/pad



78.1g/pad

Observations:

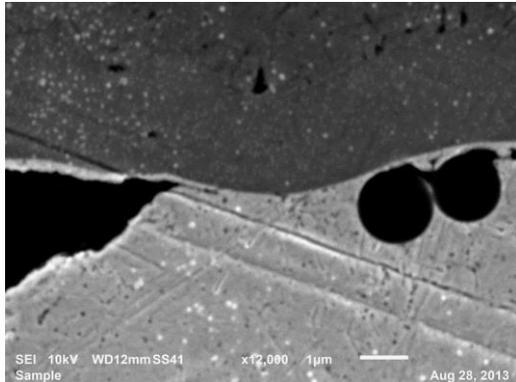
- Obvious deformation and cracks of MID pads at force 31g or above.
- Pad deformation/cracks contributing factors (bonding temp., pressure, plating quality, MID substrate)

LDS Substrate Properties

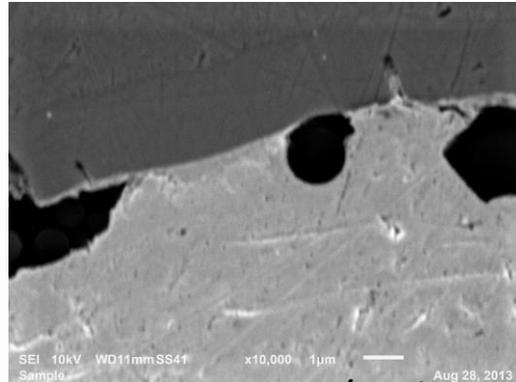
TYPICAL PROPERTIES ¹	TYPICAL VALUE	UNIT	STANDARD
MECHANICAL			
Tensile Stress, brk, Type I, 5 mm/min	135	MPa	ASTM D 638
Tensile Strain, brk, Type I, 5 mm/min	1.8	%	ASTM D 638
Tensile Modulus, 50 mm/min	10880	MPa	ASTM D 638
Flexural Stress, yld, 1.3 mm/min, 50 mm span	197	MPa	ASTM D 790
Flexural Stress, brk, 1.3 mm/min, 50 mm span	194	MPa	ASTM D 790
Flexural Modulus, 1.3 mm/min, 50 mm span	9770	MPa	ASTM D 790
Tensile Stress, break, 5 mm/min	125	MPa	ISO 527
Tensile Strain, break, 5 mm/min	1.6	%	ISO 527
Tensile Modulus, 1 mm/min	11080	MPa	ISO 527
Flexural Stress, yield, 2 mm/min	194	MPa	ISO 178
Flexural Strain, break, 2 mm/min	2	%	ISO 178
Flexural Modulus, 2 mm/min	9610	MPa	ISO 178
IMPACT			
Izod Impact, unnotched, 23°C	351	J/m	ASTM D 4812
Izod Impact, notched, 23°C	31	J/m	ASTM D 256
Izod Impact, notched 80°10'4 +23°C	2	kJ/m ²	ISO 180/1A
THERMAL			
HDT, 1.82 MPa, 3.2mm, unannealed	263	°C	ASTM D 648
CTE, -40°C to 40°C, flow	2.2E-05	1/°C	ASTM E 831
CTE, -40°C to 40°C, xflow	5.4E-05	1/°C	ASTM E 831
HDT/Af, 1.8 MPa Flatw 80°10'4 sp=64mm	261	°C	ISO 75/Af
PHYSICAL			
Density	1.55	g/cm ³	ASTM D 792
Mold Shrinkage, flow (5)	0.41	%	SABIC Method
Mold Shrinkage, xflow (5)	0.52	%	SABIC Method
Moisture Absorption (23°C / 50% RH)	0.53	%	ISO 62
ELECTRICAL			
Relative Permittivity, 1 GHz	4.2	-	ASTM D 150
Dissipation Factor, 1 GHz	0.01	-	ASTM D 150

- At the bonding temperature, the MID substrate does not provide enough support to the pads.
- However, bonding temperature cannot be lowered due to NCP curing requirement (>235°C)
- One alternative approach to minimize pad deformation is to reduce bonding forces
- Will this sacrifice the bonding interface integrity and accordingly bond reliability?

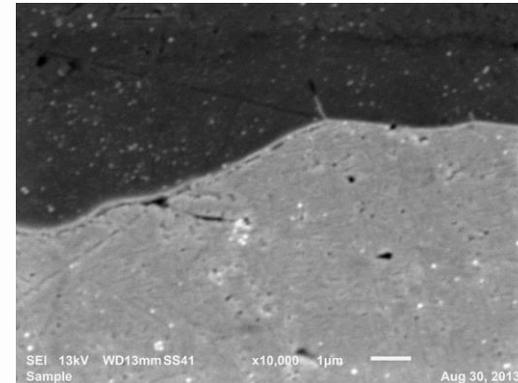
Bonding Interface Inspection



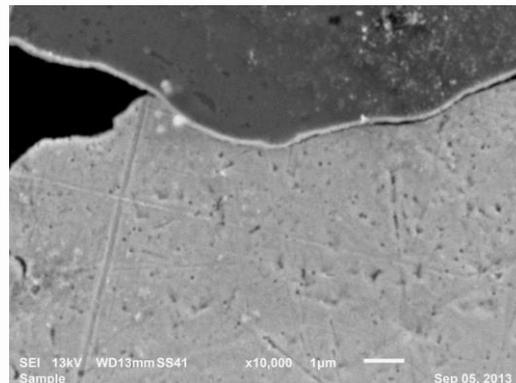
15.6g/pad



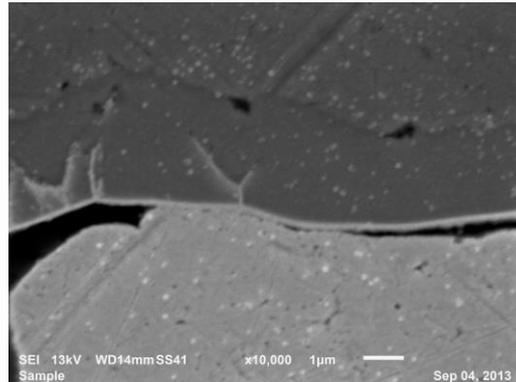
31.2g/pad



46.9g/pad



62.5g/pad

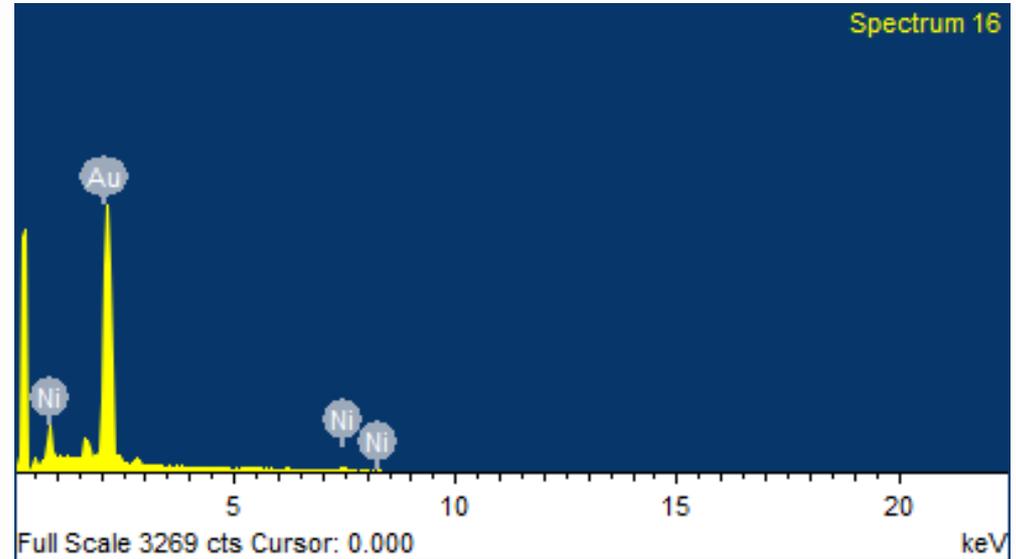
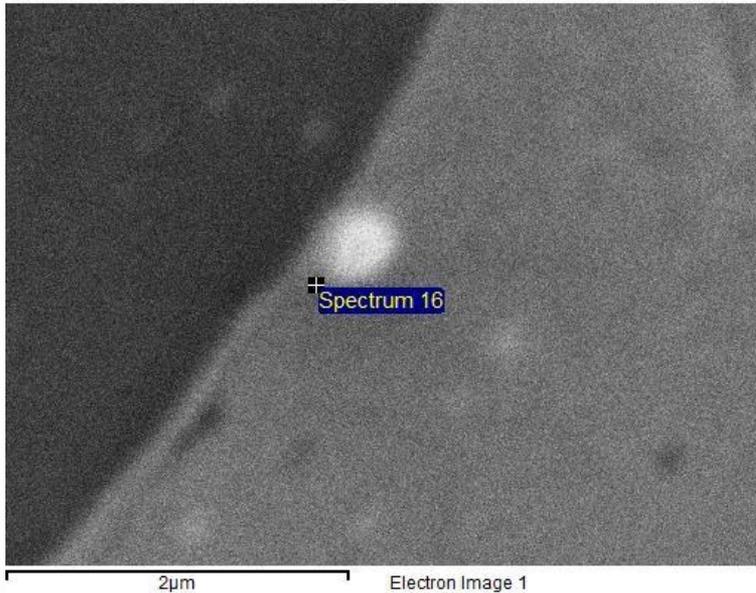


78.1g/pad

Observations:

- Some degree of gold-gold bonding formed between gold studs and gold plating for all forces at the same bonding temperature

Bonding Interface EDX



At the bonding interface, no clear intermetallic layer is observed in any SEM images, although traces of Ni are detected at the bonding interface.

TCB Bonding without NCP

- Although certain degree of bonding is formed between gold stud and gold plating, the tiny bonding area may not be strong enough to secure the chips in place.
- In order to demonstrate this, we purposely bonded a few samples without dispensing NCP material. After the process, the chips fall off easily without external forces.
- NCP material is essential to maintain a reliable bonding interface between gold stud bumps and substrate pads.
- The contraction of NCP material during cure will cause a compressive stress on the contact interface to maintain a stable bonding interface

Reliability Evaluation

- **Reliability evaluation based on IPC-SM-784 standard**
 - Thermal cycling: -55°C to +125°C (15 minutes dwell, 10 minutes ramp, 1000cycles)
 - Humidity test: 85°C, 85%, 500 hours
 - High temperature storage: 125°C, 500 hours
- **Sample sizes**
 - 78.1g/pad: 10 samples each for all above three tests
 - 15.6g/pad: 3 samples for temperature cycling
 - 46.9g/pad: 3 samples for temperature cycling
- **Results**
 - No open failures detected for all the samples

Summary

- The process for thermocompression flip chip bonding on MID substrates were successfully demonstrated.
- Significant pad deformation and cracking were observed primarily due to high bonding temperature and bonding force, and substrate material softening at high temperature.
- A certain degree of gold to gold bonding was formed at the bonding tips for all the evaluated forces. However, the tiny bonding area does not provide adequate strength to secure chips in place; contraction of NCP during curing is essential to maintain a stable bonding interface.
- Based on reliability testing results, bonding force can be optimized to reduce substrate pad deformation while maintaining bonding reliability.

Acknowledgment

- The authors would like to thank the following companies: Sabic for providing MID substrates, Nagase for providing NCP material and ASM Hong Kong for providing equipment for the evaluation work.

Thank you!

Questions?